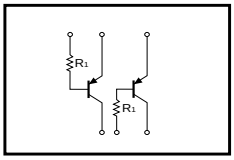
General purpose (dual digital transistors)

IMB7A

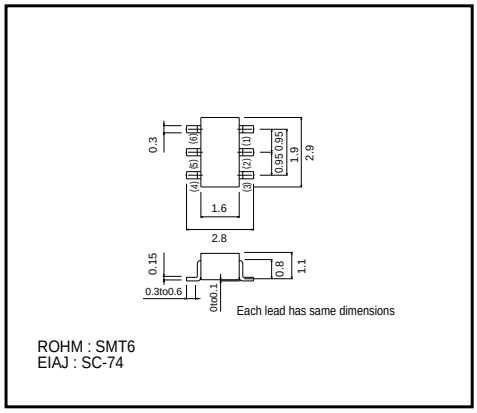
●Features

1) Two DTA143T chips in a SMT package.

●Circuit diagram



●External dimensions (Units : mm)



ROHM : SMT6
EIAJ : SC-74

●Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit	
Collector-base voltage	V_{CBO}	−50	V	
Collector-emitter voltage	V_{CEO}	−50	V	
Emitter-base voltage	V_{EBO}	−5	V	
Collector current	I_C	−100	mA	
Collector power dissipation	Pc	300(TOTAL)	mW	*
Junction temperature	Tj	150	°C	
Storage temperature	Tstg	−55~+150	°C	

* 200mW per element must not be exceeded.

●Package, marking, and packaging specifications

Type	IMB7A
Package	SMT6
Marking	B7
Code	T110
Basic ordering unit (pieces)	3000

●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	−50	–	–	V	I_C=−50μA
Collector-emitter breakdown voltage	BV_{CEO}	−50	–	–	V	I_C=−1mA
Emitter-base breakdown voltage	BV_{EBO}	−5	–	–	V	I_E=−50μA
Collector cutoff current	I_{CBO}	–	–	−0.5	μA	V_{CB}=−50V
Emitter cutoff current	I_{EBO}	–	–	−0.5	μA	V_{EB}=−4V
DC current transfer ratio	h_{FE}	100	250	600	–	V_{CE}/I_C=−5V/−1mA
Collector-emitter saturation voltage	$V_{CE(sat)}$	–	–	−0.3	V	I_C/I_B=−5mA /−0.25mA
Input resistance	R_1	3.29	4.7	6.11	kΩ	–